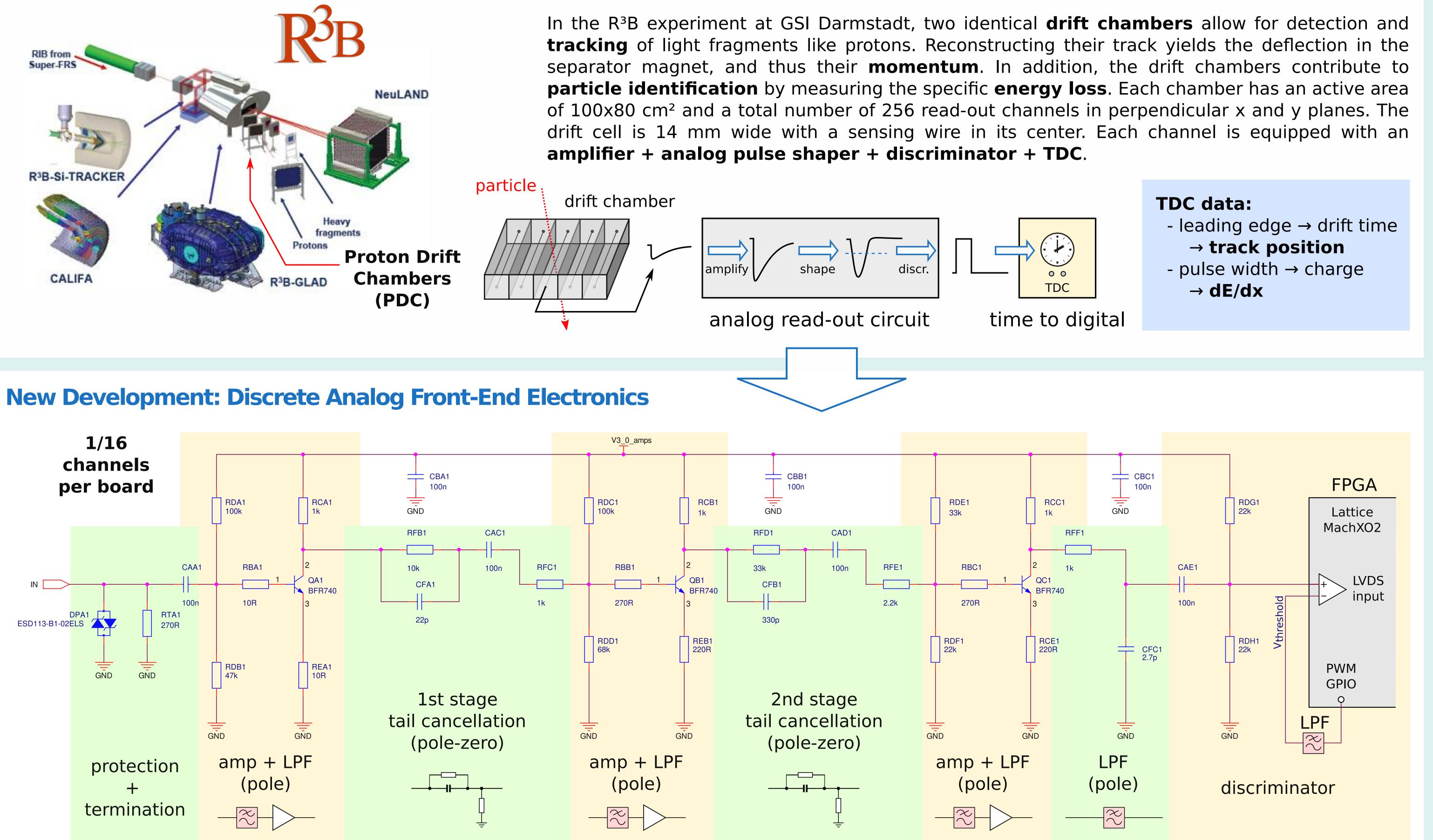
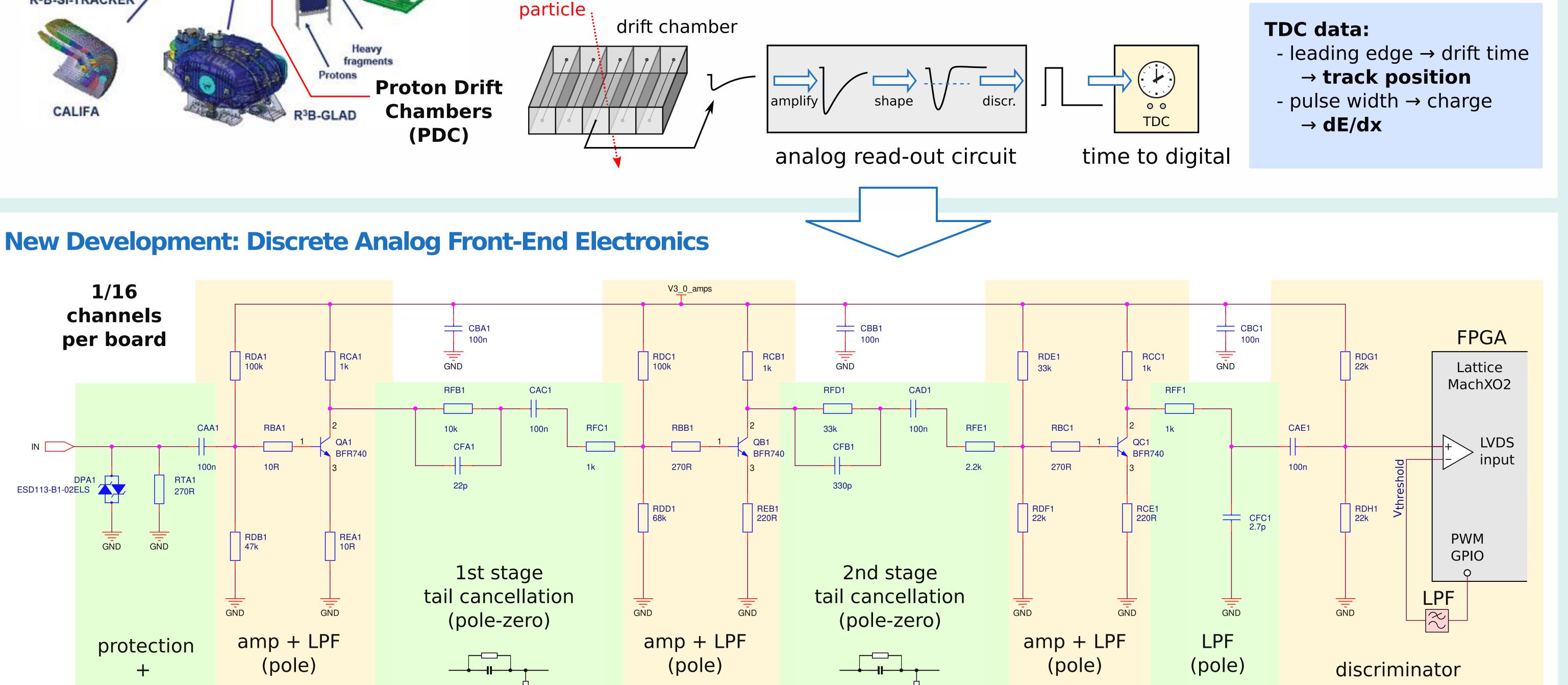
A Custom Discrete Amplifier-Shaper-Discriminator Circuit for the Drift Chambers of the R3B Experiment at GSI

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R³B Drift Chambers + Electronics



-2->

1 ch: 15x5 mm²

Specs:

- 16 channels on
- credit card sized board
- function inspired by ASD8 ASIC
- <40mW / channel
- high channel density due to 0201 SMD technology
- gain: 3.5 mV/fC
- peaking time: 14 ns
- SPI interface for slow control
- LVDS outputs to TDC
- $Z_{in} = 270 \Omega$ (customizable)
- sensitivity: ~20 fC up to ~10 pC

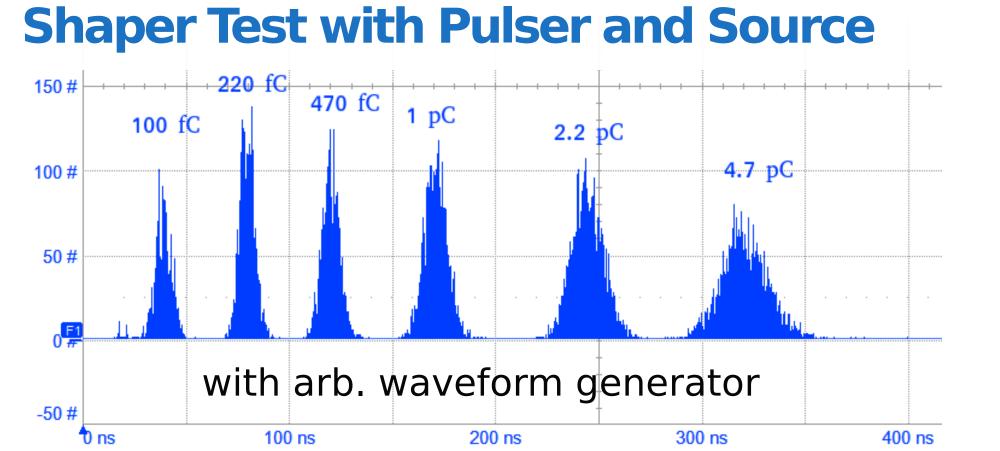
Pros:

- commonly available components
- customizable through placement variants
- good noise performance / high detection efficiency
- analog design without feedback
- \rightarrow no problems with self-oscillation (observed so far)
- little variation between channels
- individual threshold for each channel
- input impedance matched to source

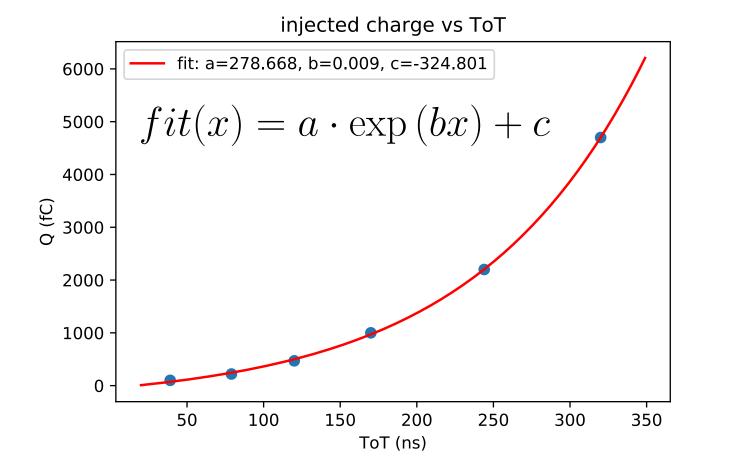
Limitations:

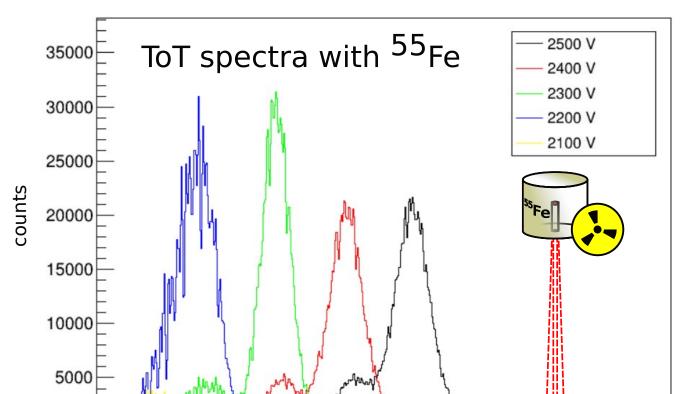
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- suited for ~kHz rather than
- ~MHz hit rates, lacks active baseline restorer
- shaper / gain not adjustable via slow control
- single ended input only

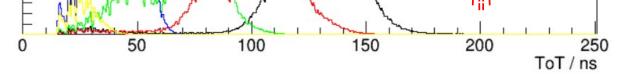


- Time over Threshold (ToT) measured with realistic ion tail pulse sample
- denoted charge includes ballistic deficit
- ToT increases logarithmically with charge - intrinsic Q precision:

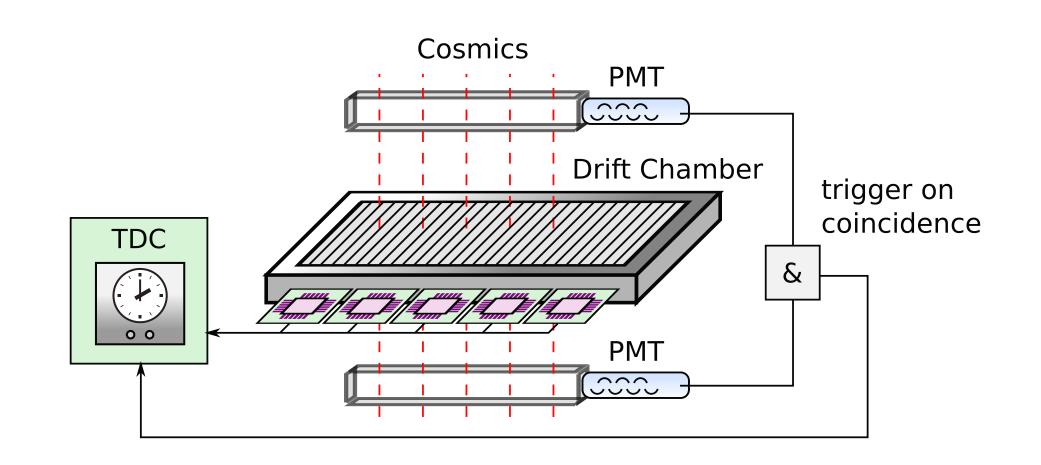




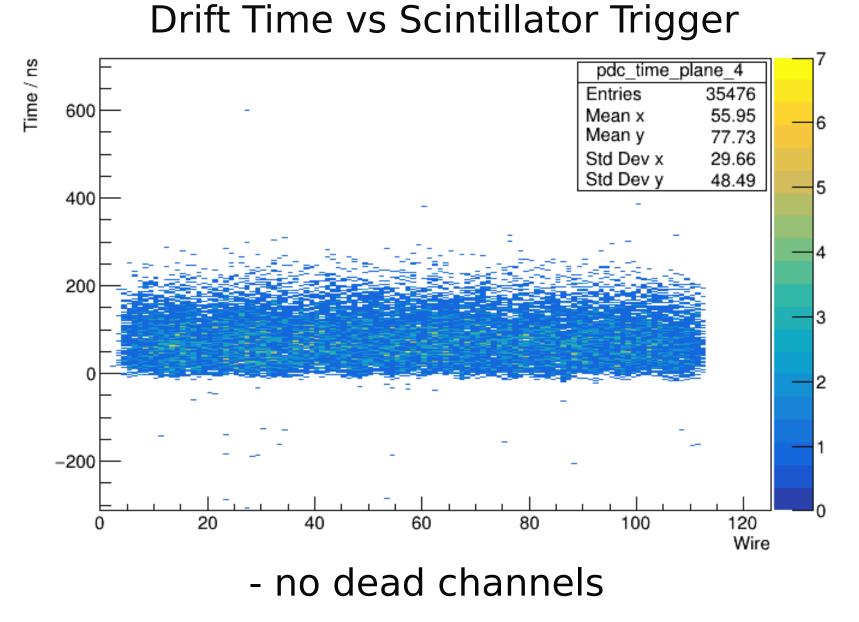
8-15% (RMS)



System Test with Cosmics



- detection efficiency $\geq 99\%$



Time over Threshold

